查询FS6S0965RC供应商 捷多邦，专业PCB打样工厂，24小时加急出货

FAIRCHILD SEMICONDUCTOR™

www.fairchildsemi.com

FS6S0965RC

Fairchild Power Switch(SPS)

Features

- Wide operating frequency range up to 150Khz
- Internal Burst mode Controller for Stand-by mode
- Pulse by pulse over current limiting
- Over current protection(Latch mode)
- Over voltage protection (Auto restart mode)
- Over load protection(Auto restart mode)
- Internal thermal shutdown function(Latch mode)
- Under voltage lockout
- Internal high voltage sense FET
- Eternal sync terminal/Soft start

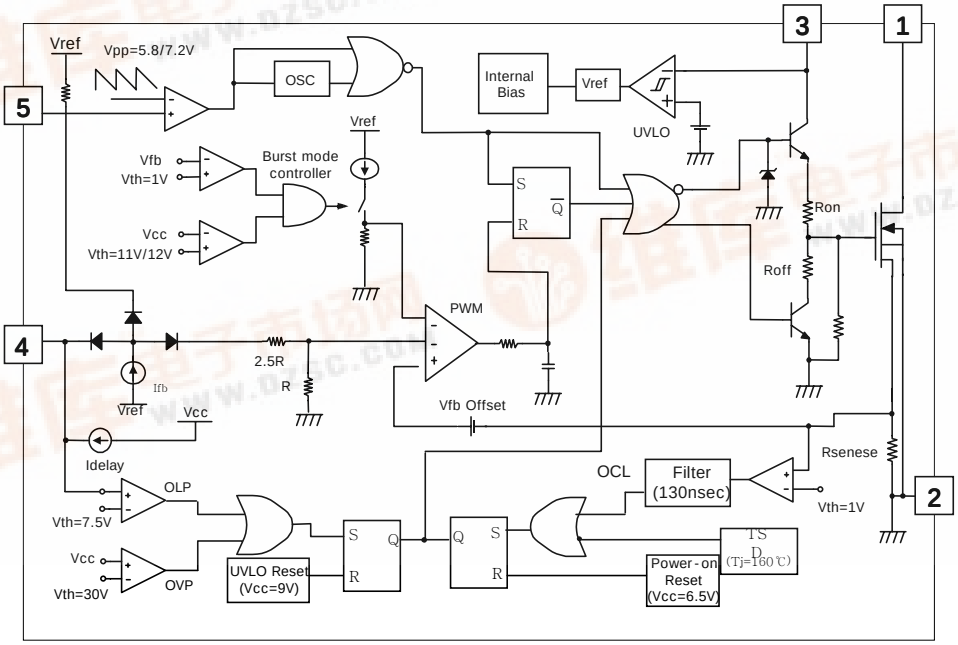
Description

The Fairchild Power Switch(SPS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(SPS) consist of high voltage power SenseFET and current mode PWM IC. Included PWM controller features integrated fixed oscillator, under voltage lock out, optimized gate turn on/turn off driver, thermal shut down protection, over voltage protection, and temperature compensated precision current sources for loop compensation and fault protection circuitry. compared to discrete MOSFET and controller or RCC switching converter solution, a SPS can reduce total component count, design size, and weight and at the same time increase efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective monitor power supply.

TO-220-5L

1

Internal Block Diagram



Rev.1.0.0

找PDF 维库一下 pdf.dzsc.com

©2001 Fairchild Semiconductor Corporation

Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source(GND) voltage [1]	V_{DSS}	650	V
Drain-Gate Voltage (R_{GS}=1MΩ)	V_{DGR}	650	V
Gate-source (GND) Voltage	V_{GS}	±30	V
Drain current pulsed [2]	I_{DM}	32.4	A_{DC}
Single pulsed avalanche energy [3]	E_{AS}	515	mJ
Single Pulsed Avalanche current [4]	I_{AS}	25	A
Continuous drain current (Tc = 25°C)	I_D	8.1	A_{DC}
Continuous drain current (T_C=100°C)	I_D	5.1	A_{DC}
Supply voltage	V_{CC}	35	V
Input Voltage Range	V_{FB}	–0.3 to V_{CC}	V
	V_{S_S}	–0.3 to 10	V
Total Power Dissipation	P_D(Watt H/S)	155	W
	Derating	1.243	W/°C
Operating junction temperature	T_j	+160	°C
Operating Ambient Temperature	T_A	–25 to +85	°C
Storage Temperature range	T_{STG}	–55 to +150	°C

Notes:
1. Tj=25°C to 150°C
2. Repetitive rating: Pulse width limited by maximum junction temperature
3. L=14.5mH, starting Tj=25°C
4. L=13uH, starting Tj=25°C

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	650	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS}=650V, V_{GS}=0V	-	-	200	μA
		V_{DS}=520V V_{GS}=0V, T_C=125°C	-	-	300	μA
Static drain-source on resistance (note)	$R_{DS(ON)}$	V_{GS}=10V, I_D=1.8A	-	1.0	1.2	Ω
Forward transconductance (note)	gfs	V_{DS}=50V, I_D=1.8A	-	-	-	S
Input capacitance	Ciss	V_{GS}=0V, V_{DS}=25V, f = 1MHz	-	1300	-	pF
Output capacitance	Coss		-	135	-	
Reverse transfer capacitance	Crss		-	25	-	
Turn on delay time	td(on)	V_{DD}=325V, I_D=6.5A (MOSFET switching time are essentially independent of operating temperature)	-	25	-	nS
Rise time	tr		-	75	-	
Turn off delay time	td(off)		-	130	-	
Fall time	tf		-	70	-	
Total gate charge (gate-source+gate-drain)	Qg	V_{GS}=10V, I_D=6.5A, V_{DS}=520V (MOSFET Switching time are Essentially independent of Operating temperature)	-	45	60	nC
Gate-source charge	Qgs		-	8	-	
Gate-drain (Miller) charge	Qgd		-	21	-	

Note:

Pulse test : Pulse width ≤ 300μS, duty 2%

$$S = \frac{1}{R}$$

Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start threshold voltage	V_{START}	V_{FB}=GND	14	15	16	V
Stop threshold voltage	V_{STOP}	V_{FB}=GND	8	9	10	V
SENSEFET SECTION						
Drain to PKG Breakdown voltage	BVpkg	60HZ AC, Ta=25°C	3500	-	-	V
Drain to Source Breakdown voltage	BVdss	Vdrain = 650V, Ta=25°C	650	-	-	V
Drain to Source Leakage current	Idss	Vdrain = 650V, Ta=25°C	-	-	300	uA
OSCILLATOR SECTION						
Initial Frequency	F_{OSC}	-	22	25	28	kHz
Voltage Stability	FSTABLE	12V ≤ Vcc ≤ 23V	0	1	3	%
Temperature Stability (note4)	ΔFOSC	-25°C ≤ Ta ≤ 85°C	0	±5	±10	%
Maximum duty cycle	DMAX	-	92	95	98	%
Minimum Duty Cycle	DMIN	-	-	-	0	%
FEEDBACK SECTION						
Feedback source current	I_{FB}	V_{FB}=GND	0.7	0.9	1.1	mA
Shutdown Feedback voltage	V_{SD}	Vfb ≥ 6.9V	6.9	7.5	8.1	V
Shutdown delay current	Idelay	V_{FB}=5V	1.6	2.0	2.4	µA
PROTECTION SECTION						
Over Voltage Protection	V_{OVP}	Vsync ≥ 11V	27	30	33	V
Over Current Latch Voltage (Note2)	V_{OCL}	-	0.9	1.0	1.1	V
Thermal Shutdown Temp.(Note4)	TSD	-	140	160	-	°C

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Sync & SOFTSTART SECTION						
Softstart Vortage	V_{SS}	Vfb=2	4.7	5.0	5.3	V
Softstart Current	I_{SS}	Vss=V	0.8	1.0	1.2	mA
Sync High Threshold Voltage	V_{SYNCH}	Vcc=16V,Vfb=5V	-	7.2	-	V
Sync Low Threshold Voltage	V_{SYNCL}	Vcc=16V,Vfb=5V	-	5.8	-	V
BURST MODE SECTION						
Burst mode Low Threshold Voltage	V_{BURL}	Vfb=0V	10.4	11.0	11.6	V
Burst mode High Threshold Voltage	V_{BURH}	Vfb=0V	11.4	12.0	12.6	V
Burst mode Enable Feedback Voltage(Note4)	V_{BEN}	Vcc=10.5V	0.7	1.0	1.3	V
Burst mode Peak Current Limit(Note3)	I_{BU_PK}	Vcc=10.5V	0.6	0.85	1.1	V
Burst mode Frequency	F_{BUR}	Vcc=10.5V, Vfb=0V	40	50	60	KHz
CURRENT LIMIT(SELF-PROTECTION)SECTION						
Peak Current Limit(Note3)	I_{OVER}	-	5.28	6.0	6.72	A
TOTAL DEVICE SECTION						
Start Up current	I_{START}	Vfb=GND, V_{CC}=14V	-	0.1	0.17	mA
Operating supply current (Note1)	I_{OP}	Vfb=GND, V_{CC}=16V	-	10	15	mA
	$I_{OP(MIN)}$	Vfb=GND, V_{CC}=10V				
	$I_{OP(MAX)}$	Vfb=GND, V_{CC}=28V				

Note:

(1) These parameters is the current flowing in the Control IC.

(2) These parameters, although guaranteed, are tested in EDS(wafer test) process.

(3) These parameters indicate Inductor Current.

(4) These parameters, although guranteed at the design, are not tested in massing production.

Typical Performance Characteristics

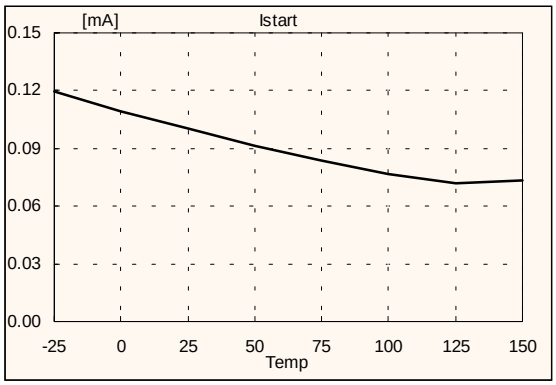


Figure 1. Start Up Current vs. Temp.

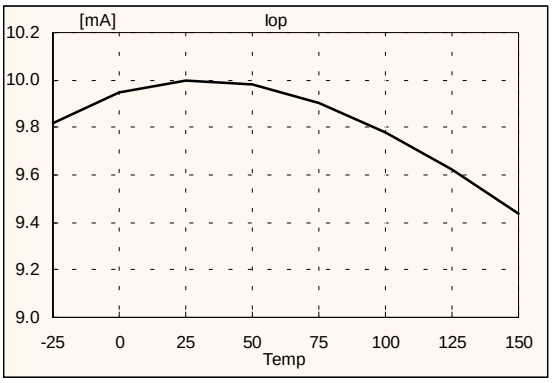


Figure 2. Operating Supply Current vs. Temp.

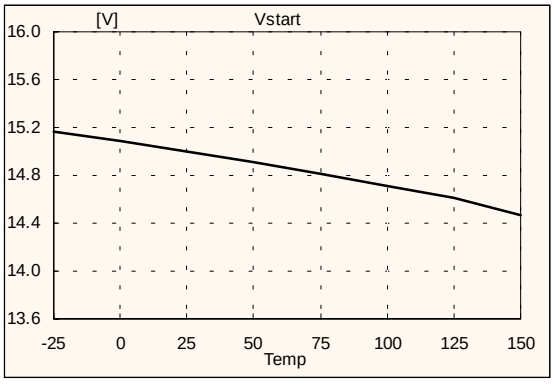


Figure 3. Start Threshold Voltage vs. Temp.

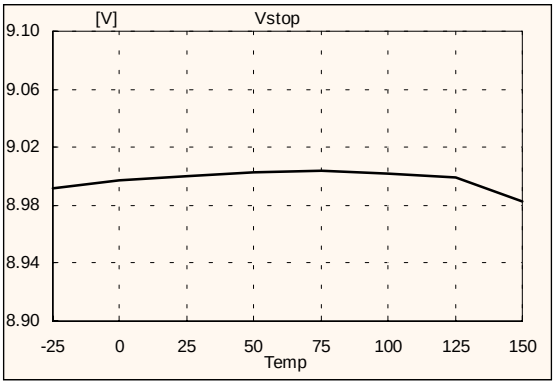


Figure 4. Stop Threshold Voltage vs. Temp.

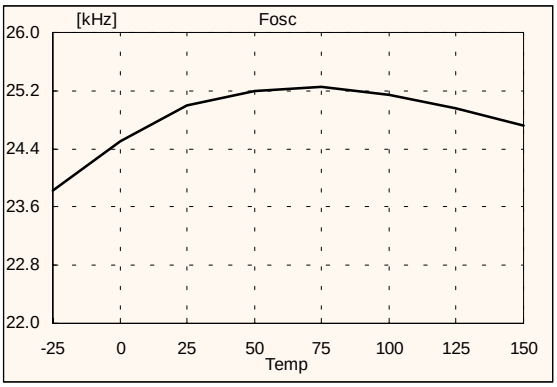


Figure 5. Initial Frequency vs. Temp.

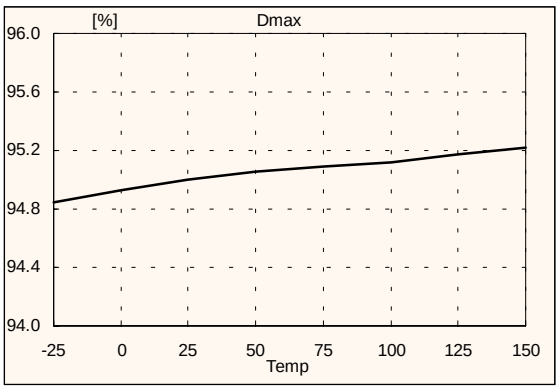


Figure 6. Maximum Duty vs. Temp.

Typical Performance Characteristics (Continued)

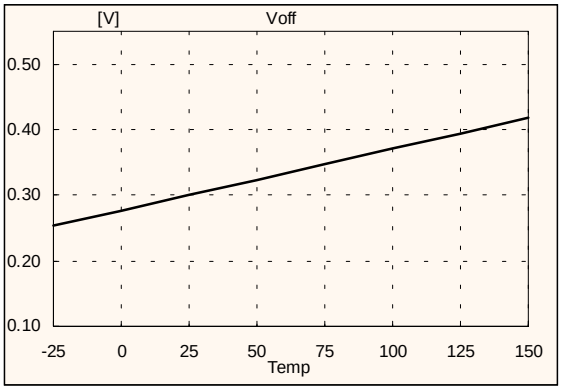


Figure 7. Feedback Offset Voltage vs. Temp.

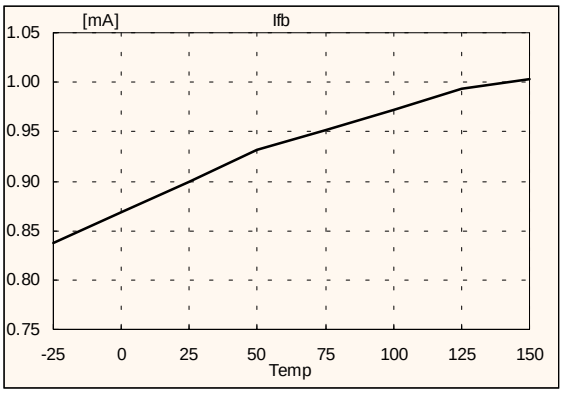


Figure 8. Feedback Source Current vs. Temp.

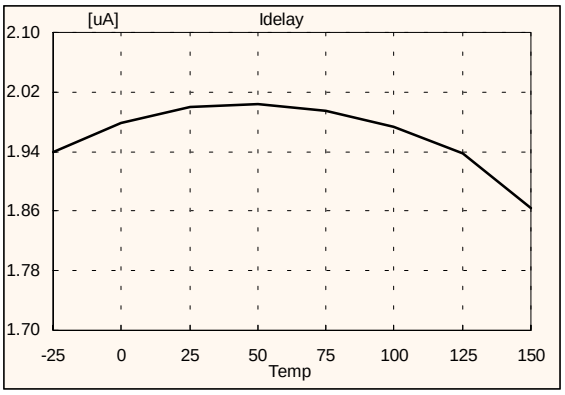


Figure 9. Shutdown Delay Current vs. Temp.

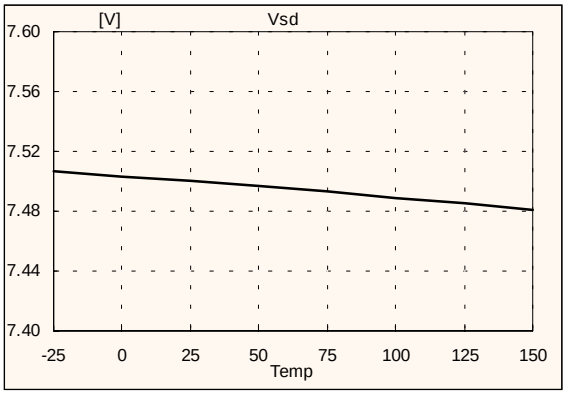


Figure 10. Shutdown Feedback Voltage vs. Temp.

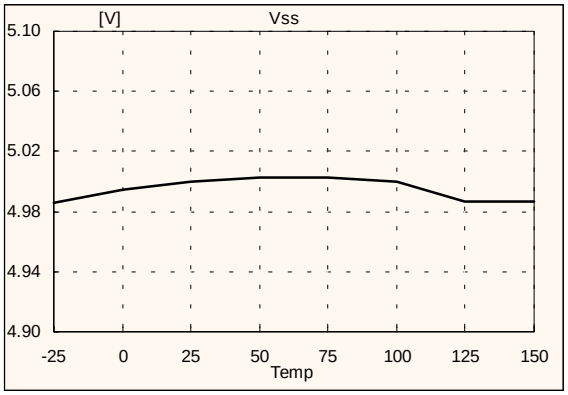


Figure 11. Softstart Voltage vs. Temp.

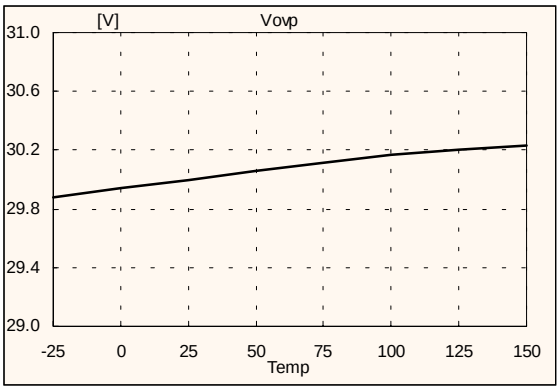


Figure 12. Over Voltage Protection vs. Temp.

Typical Performance Characteristics (Continued)

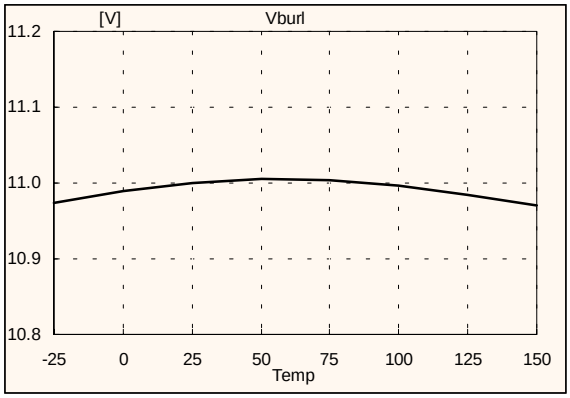


Figure 13. Burst Mode Low Voltage vs. Temp.

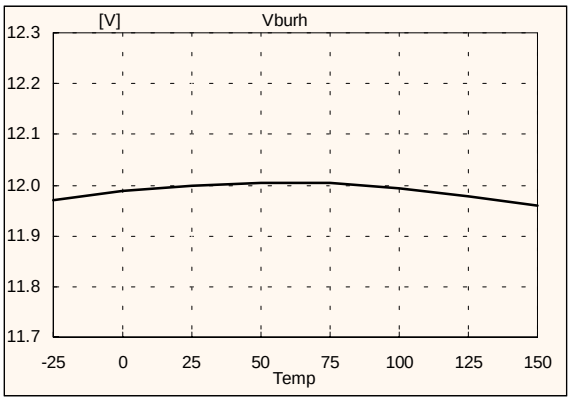


Figure 14. Burst Mode High Voltage vs. Temp.

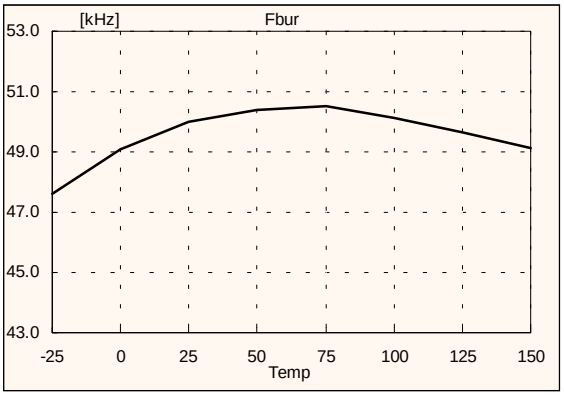


Figure 15. Burst Mode Frequency vs. Temp.

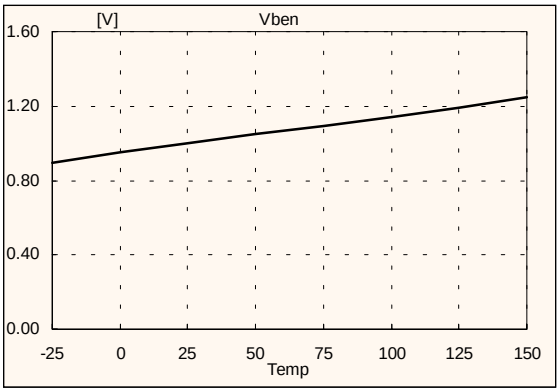


Figure 16. Burst Mode Enable Voltage vs. Temp.

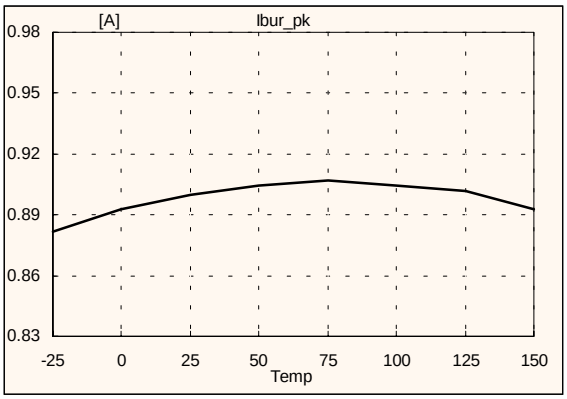


Figure 17. Burst Mode Peak Current vs. Temp.

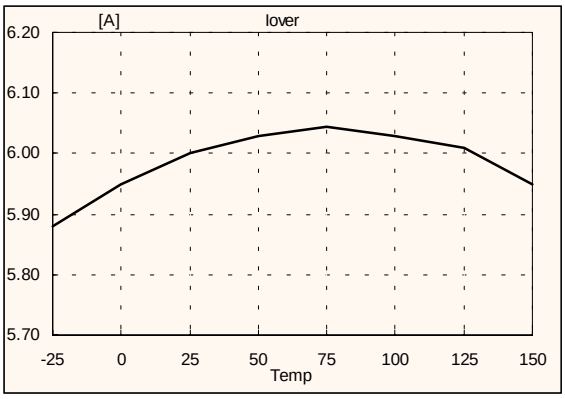
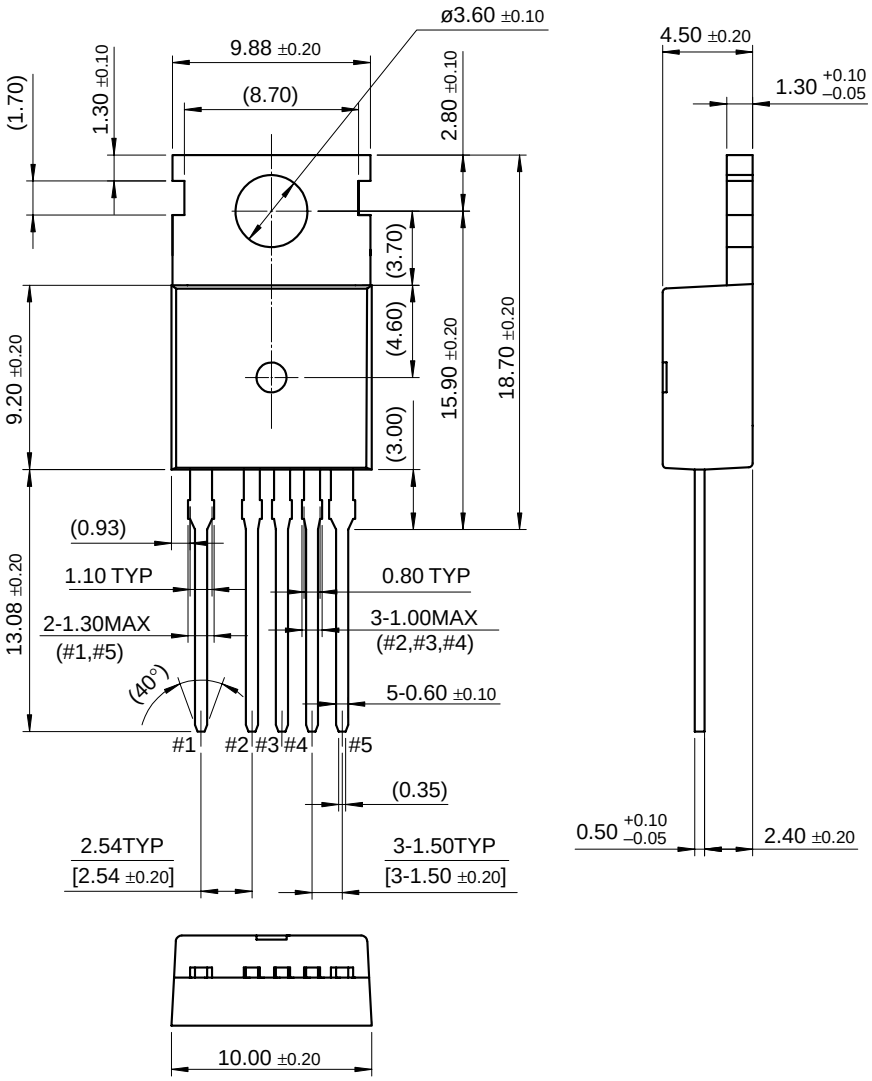


Figure 18. Peak Current Limit vs. Temp.

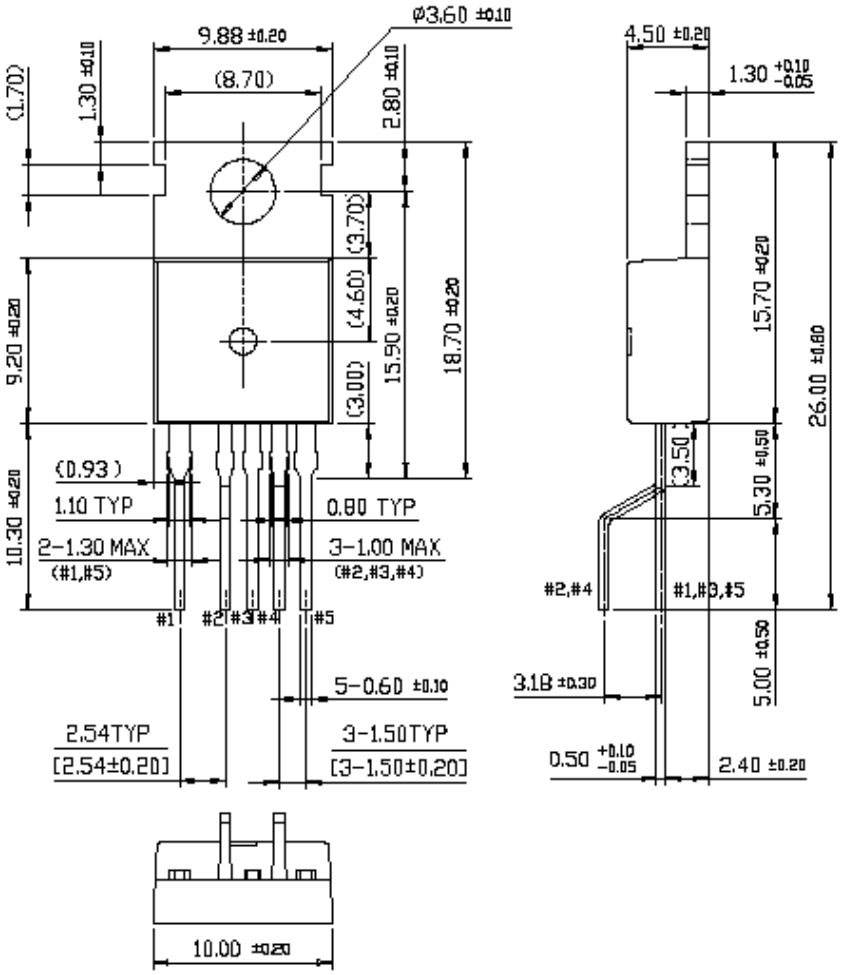
Package Dimensions

TO-220-5L



Package Dimensions (Continued)

TO-220-5L(Forming)



Ordering Information

Product Number	Package	Marking Code	BVdss	Rds(on)
FS6S0965RC-TU	TO-220-5L	6S0965RC	650V	1.0
FS6S0965RC-YDTU	TO-220-5L(Forming)			

TU : Non Forming Type
YDTU : Forming Type

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.